

# isc N-Channel MOSFET Transistor

# FCPF099N65S3

### • FEATURES

- With TO-220 packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### • APPLICATIONS

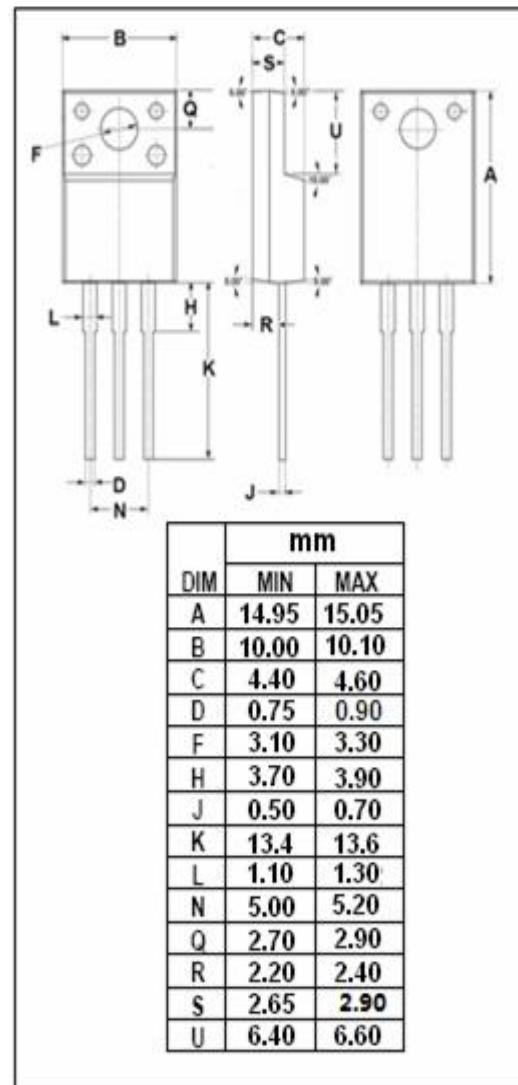
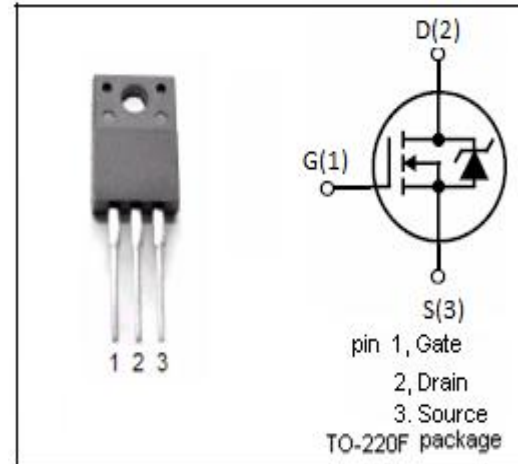
- Power supply
- Switching applications

### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage	650	V
V <sub>GSS</sub>	Gate-Source Voltage	±30	V
I <sub>D</sub>	Drain Current-Continuous; @T <sub>c</sub> =25°C T <sub>c</sub> =100°C	30 19	A
I <sub>DM</sub>	Drain Current-Single Pulsed	75	A
P <sub>D</sub>	Total Dissipation	43	W
T <sub>j</sub>	Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(ch-c)</sub>	Channel-to-case thermal resistance	2.94	°C/W
R <sub>th(ch-a)</sub>	Channel-to-ambient thermal resistance	62.5	°C/W



**isc N-Channel MOSFET Transistor****FCPF099N65S3****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=1.0mA$	100			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=3.0mA$	2.5		4.5	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=15A$		85	99	$m\Omega$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 30V; V_{DS}=0V$			$\pm 0.1$	$\mu A$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=650V; V_{GS}=0V$			1	$\mu A$
$V_{SDF}$	Diode forward voltage	$I_{SD}=15A, V_{GS}=0V$			1.2	V